

IN THE SPECIFICATION:

Please substitute the paragraph starting at page 2, line 10 and ending at line 20, with the following paragraph. A marked-up copy of this paragraph, showing the changes made thereto, is attached.

A --Referring to FIGS. 14A and 14B, as high energy electromagnetic waves 108 such as X rays enter the detector, an electric charge is generated in semiconductor substrates 106 typically made of Si, GaAs, CdTe or HgI<sub>2</sub> and transferred to readout circuits 116 of integrated circuit chips 110a and 110b by way of electrodes 114, bumps 120 and electrodes 119. Electrodes 134a through 134e and electrodes 130a through 130d as well as bumps 136 are provided to connect the semiconductor substrates 106 and the integrated circuit chips 110a and 110b.--

Please substitute the paragraph starting at page 2, line 21 and ending at page 3, line 6, with the following paragraph. A marked-up copy of this paragraph, showing the changes made thereto, is attached.

A2 --U.S. Patent No. 5,198,673 describes a direct type sensor equipped with protection diodes. FIG. 15 of the accompanying drawings is a schematic block diagram of the read/reset circuit of a direct type sensor 160 having protection diodes as disclosed in the above patent document. Referring to FIG. 15, there are shown scan switches 222a and 222b connected to scan wires 220a and 220b and output wires 230, the latter by turn being connected to sample-and-hold amplifiers (read circuits) 235 and reset circuits 237. The scan switches are also connected to sensors 210, high voltage sources 212, storage capacitors 214 and overvoltage protection elements (protection diodes) 240.--